STP20NK50Z - STW20NK50Z

N-CHANNEL 500V - 0.23Ω - 20A TO-220/TO-247
Zener-Protected SuperMESH™Power MOSFET

TARGET DATA

TYPE	V$_{DSS}$	R$_{DS(on)}$	I$_D$	Pw
STP20NK50Z	500 V	< 0.27 Ω	20 A	190 W
STW20NK50Z	500 V	< 0.27 Ω	20 A	190 W

- TYPICAL R$_{DS}$(on) = 0.23 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATIBILITY


TO-220   TO-247
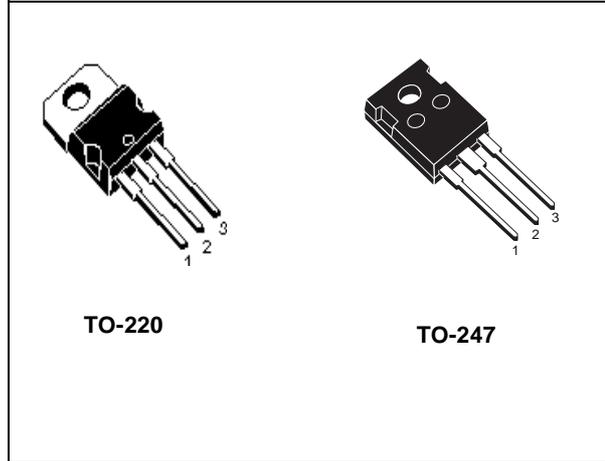
DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

INTERNAL SCHEMATIC DIAGRAM

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES, ADAPTORS AND PFC
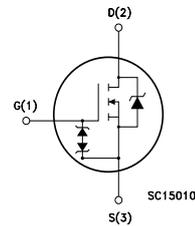
ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP20NK50Z	P20NK50Z	TO-220	TUBE
STW20NK50Z	W20NK50Z	TO-247	TUBE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP20NK50Z	STW20NK50Z	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	500		V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	500		V
V_{GS}	Gate- source Voltage	± 30		V
I_D	Drain Current (continuos) at T_C = 25°C	20	20	A
I_D	Drain Current (continuos) at T_C = 100°C	10	10	A
I_{DM} (•)	Drain Current (pulsed)	64	64	A
P_{TOT}	Total Dissipation at T_C = 25°C	190	190	W
	Derating Factor	1.51	1.51	W/°C
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=1.5KΩ)	4000		V
dv/dt (1)	Peak Diode Recovery voltage slope	4.5		V/ns
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 150 -55 to 150		°C °C

(•) Pulse width limited by safe operating area
(1) I_{SD} ≤20A, di/dt ≤200A/μs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ T_{JMAX}.
(*) Limited only by maximum temperature allowed

THERMAL DATA

		TO-220	TO-247	
Rthj-case	Thermal Resistance Junction-case Max	0.66	0.66	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	50	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	20	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	TBD	mJ

GATE-SOURCE ZENER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	Igs=± 1mA (Open Drain)	30			V

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

ELECTRICAL CHARACTERISTICS (TCASE =25°C UNLESS OTHERWISE SPECIFIED)
ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0	500			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating, T_C = 125 °C			1 50	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	3	3.75	4.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 10 A		0.23	0.27	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} = 8 V, I_D = 10 A		TBD		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		2600 400 55		pF pF pF
$C_{oss\ eq.}$ (3)	Equivalent Output Capacitance	V_{GS} = 0V, V_{DS} = 0V to 400V		TBD		pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 250 V, I_D = 10 A R_G = 4.7Ω V_{GS} = 10 V (Resistive Load see, Figure 3)		TBD TBD		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 400V, I_D = 20 A, V_{GS} = 10V		95 TBD TBD		nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 250 V, I_D = 10 A R_G = 4.7Ω V_{GS} = 10 V (Resistive Load see, Figure 3)		TBD TBD		ns ns
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 400V, I_D = 20 A, R_G = 4.7Ω, V_{GS} = 10V (Inductive Load see, Figure 5)		TBD TBD TBD		ns ns ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (2)	Source-drain Current Source-drain Current (pulsed)				TBD TBD	A A
V_{SD} (1)	Forward On Voltage	I_{SD} = 20 A, V_{GS} = 0			TBD	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 20 A, di/dt = 100A/µs V_{DD} = 35V, T_j = 150°C (see test circuit, Figure 5)		TBD TBD TBD		ns µC A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.
3. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Fig. 1: Unclamped Inductive Load Test Circuit

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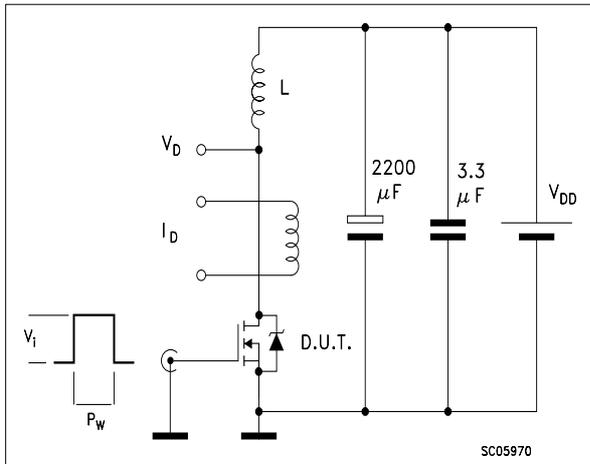
**Fig. 2:** Unclamped Inductive Waveform

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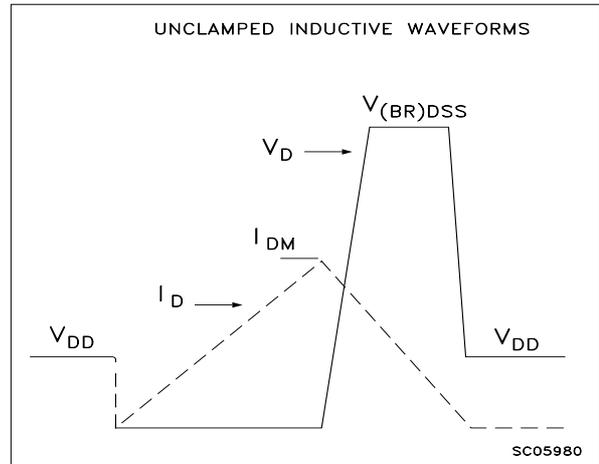
Fig. 3: Switching Times Test Circuit For Resistive Load

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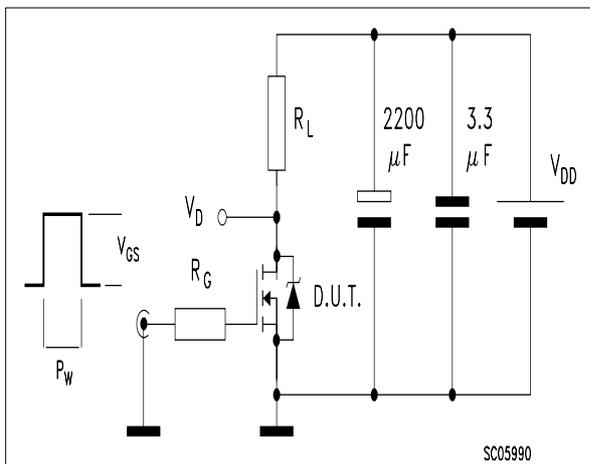
Fig. 4: Gate Charge test Circuit

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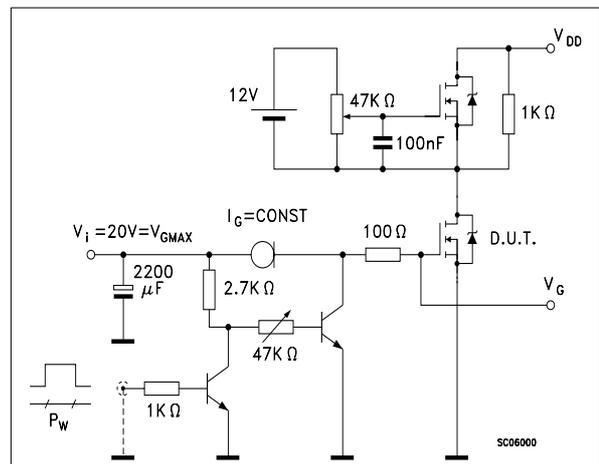
**Fig. 5:** Test Circuit For Inductive Load Switching And Diode Recovery Times

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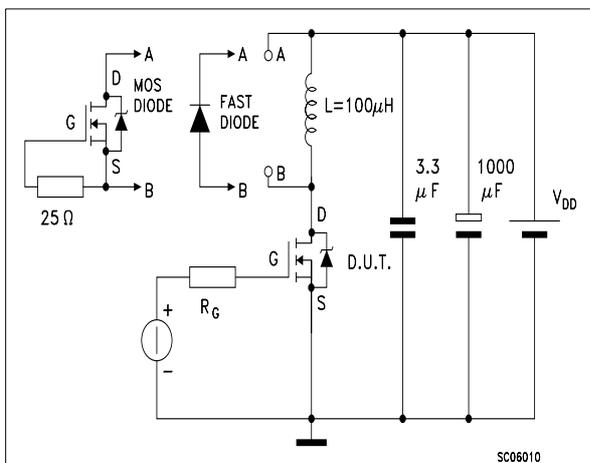
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151

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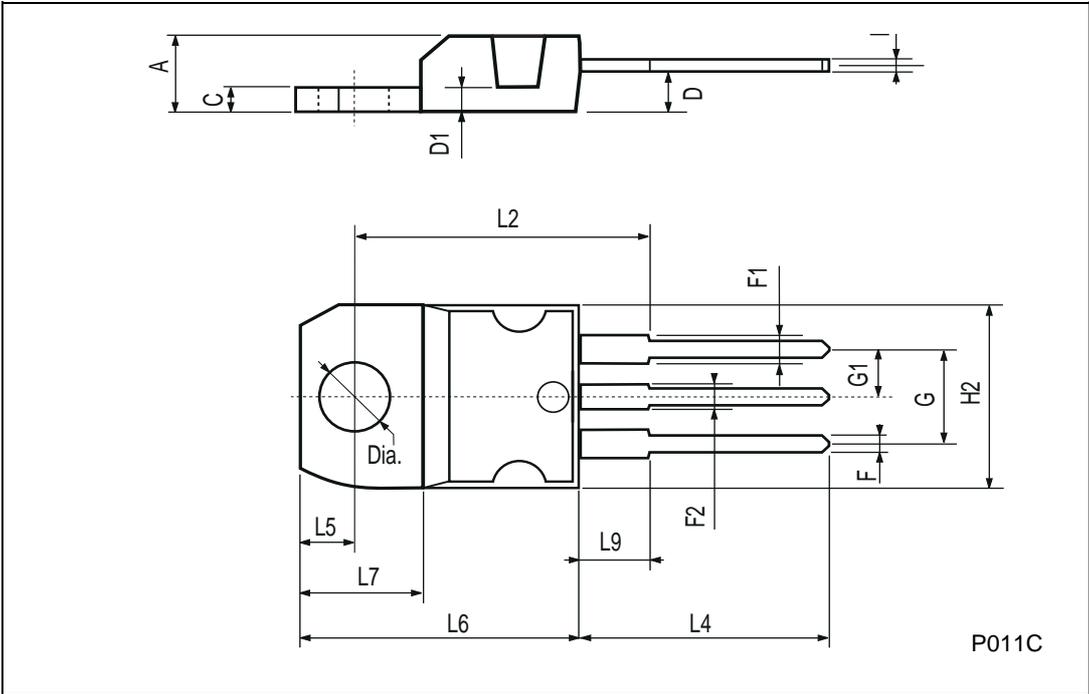
TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
D	2.20		2.60	0.08		0.10
E	0.40		0.80	0.015		0.03
F	1		1.40	0.04		0.05
F1		3			0.11	
F2		2			0.07	
F3	2		2.40	0.07		0.09
F4	3		3.40	0.11		0.13
G		10.90			0.43	
H	15.45		15.75	0.60		0.62
L	19.85		20.15	0.78		0.79
L1	3.70		4.30	0.14		0.17
L2		18.50			0.72	
L3	14.20		14.80	0.56		0.58
L4		34.60			1.36	
L5		5.50			0.21	
M	2		3	0.07		0.11
V		5º			5º	
V2		60º			60º	
Dia	3.55		3.65	0.14		0.143